

Nandakishor Yadav

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

31
papers

198
citations

9
h-index

13
g-index

38
ext. papers

264
ext. citations

1.9
avg, IF

3.54
L-index

#	Paper	IF	Citations
31	Stable, Low Power and Bit-Interleaving Aware SRAM Memory for Multi-Core Processing Elements. <i>Electronics (Switzerland)</i> , 2021 , 10, 2724	2.6	1
30	Design and Analysis of Cyl GAA-TFET-Based Cross-Coupled Voltage Doubler Circuit. <i>Lecture Notes in Electrical Engineering</i> , 2021 , 69-79	0.2	
29	A Novel Ultra-Low Power 8T SRAM-Based Compute-in-Memory Design for Binary Neural Networks. <i>Electronics (Switzerland)</i> , 2021 , 10, 2181	2.6	0
28	Ultra-Low Power and High-Throughput SRAM Design to Enhance AI Computing Ability in Autonomous Vehicles. <i>Electronics (Switzerland)</i> , 2021 , 10, 256	2.6	2
27	A Novel FPGA Accelerator Design for Real-Time and Ultra-Low Power Deep Convolutional Neural Networks Compared With Titan X GPU. <i>IEEE Access</i> , 2020 , 8, 105455-105471	3.5	11
26	Novel CNN-Based AP2D-Net Accelerator: An Area and Power Efficient Solution for Real-Time Applications on Mobile FPGA. <i>Electronics (Switzerland)</i> , 2020 , 9, 832	2.6	7
25	Design of a Voltage to Time Converter with High Conversion Gain for Reliable and Secure Autonomous Vehicles. <i>Electronics (Switzerland)</i> , 2020 , 9, 384	2.6	2
24	A Reactive and On-Chip Sensor Circuit for NBTI and PBTI Resilient SRAM Design. <i>Electronics (Switzerland)</i> , 2020 , 9, 326	2.6	0
23	Sensitive, Linear, Robust Current-To-Time Converter Circuit for Vehicle Automation Application. <i>Electronics (Switzerland)</i> , 2020 , 9, 490	2.6	1
22	Design and Development of BTI Model and 3D InGaAs HEMT-Based SRAM for Reliable and Secure Internet of Things Application. <i>Electronics (Switzerland)</i> , 2020 , 9, 469	2.6	0
21	Low-Power RTL Code Generation for Advanced CNN Algorithms toward Object Detection in Autonomous Vehicles. <i>Electronics (Switzerland)</i> , 2020 , 9, 478	2.6	5
20	Symmetric dual gate insulator-based FinFET module and design window for reliable circuits. <i>Micro and Nano Letters</i> , 2019 , 14, 317-322	0.9	1
19	SUBHDIP: process variations tolerant subthreshold Darlington pair-based NBTI sensor circuit. <i>IET Computers and Digital Techniques</i> , 2019 , 13, 243-249	0.9	5
18	On-Chip Adaptive Body Bias for Reducing the Impact of NBTI on 6T SRAM Cells. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2018 , 31, 242-249	2.6	27
17	Analog/RF characteristics of a 3D-Cyl underlap GAA-TFET based on a Ge source using fringing-field engineering for low-power applications. <i>Journal of Computational Electronics</i> , 2018 , 17, 1650-1657	1.8	12
16	NMOS only Schmitt trigger circuit for NBTI resilient CMOS circuits. <i>Electronics Letters</i> , 2018 , 54, 868-870	1.1	6
15	Process Variation and NBTI Resilient Schmitt Trigger for Stable and Reliable Circuits. <i>IEEE Transactions on Device and Materials Reliability</i> , 2018 , 18, 546-554	1.6	12

14	An efficient NBTI sensor and compensation circuit for stable and reliable SRAM cells. <i>Microelectronics Reliability</i> , 2018 , 87, 15-23	1.2	11
13	Impact of varying carbon concentration in SiC S/D asymmetric dual-k spacer for high performance and reliable FinFET. <i>Journal of Semiconductors</i> , 2018 , 39, 104001	2.3	2
12	Stable, Reliable, and Bit-Interleaving 12T SRAM for Space Applications: A Device Circuit Co-Design. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2017 , 30, 276-284	2.6	26
11	Systematically Optimized Ketoprofen-Loaded Novel Proniosomal Formulation for Periodontitis: In Vitro Characterization and In Vivo Pharmacodynamic Evaluation. <i>AAPS PharmSciTech</i> , 2017 , 18, 1863-1880 ⁹	3.9	13
10	Analysis of trap-assisted tunnelling in asymmetrical underlap 3D-cylindrical GAA-TFET based on hetero-spacer engineering for improved device reliability. <i>Micro and Nano Letters</i> , 2017 , 12, 982-986	0.9	10
9	Subthreshold darlington pair based NBTI sensor for reliable CMOS circuits 2017 ,		2
8	LISOCHIN: An NBTI Degradation Monitoring Sensor for Reliable CMOS Circuits. <i>Communications in Computer and Information Science</i> , 2017 , 441-451	0.3	2
7	Systematically optimized coenzyme q10-loaded novel proniosomal formulation for treatment of photo-induced aging in mice: characterization, biocompatibility studies, biochemical estimations and anti-aging evaluation. <i>Journal of Drug Targeting</i> , 2016 , 24, 257-71	5.4	23
6	A novel stability and process sensitivity driven model for optimal sized FinFET based SRAM. <i>Microelectronics Reliability</i> , 2015 , 55, 1131-1143	1.2	2
5	A New Sensitivity-Driven Process Variation Aware Self-Repairing Low-Power SRAM Design 2014 ,		2
4	A sensitivity driven 10T SRAM cell to mitigate process variation via selective back-gate biasing 2014 ,		1
3	NBTI aware IG-FinFET based SRAM design using adaptable trip-point sensing technique 2014 ,		5
2	Double-gate FinFET process variation aware 10T SRAM cell topology design and analysis 2013 ,		3
1	Self-restoring PVT aware independently-controlled Gate FinFET based 10T SRAM cell 2013 ,		1